

### **REMARKS/ARGUMENTS**

The applicants' attorneys appreciate the Examiner's thorough search and remarks.

Claim 1 has been rejected under 35 U.S.C. §112, first paragraph, as failing to comply with the written description requirement. To the extent understood, it has been alleged that claim 1 fails because the specification does not set forth a representative number of species to claim a genus.

Claim 1 is directed at a P-channel MOSgated device which includes a gate oxide formed of radiation hardened silicon dioxide that is less than 1000Å thick. Claim 1 does not extend to all MOSgated devices as alleged. Furthermore, claim 1 is specifically directed at a P-channel MOSgated device with a radiation hardened silicon dioxide gate oxide which can resist "threshold voltage shift due to total radiation dose", and can resist "single event gate rupture due to a significant effect". The specification has set forth at least one device according to claim 1, and a method for making the same. It is respectfully submitted that there is adequate support for the subject matter of claim 1. Withdrawal of the rejection is, therefore, requested.

Claim 1 was also rejected under 35 U.S.C. §112, second paragraph. Claim 1 has been amended and is now believed to be in compliance with section 112. Reconsideration is requested.

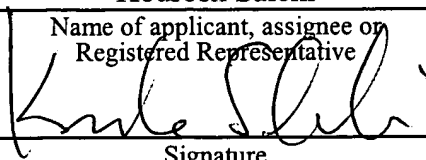
Claim 1 has been rejected under 35 U.S.C. §103(a) as obvious over Williams, Kalnitsky and Wolf. This ground of rejection only includes Wolf as an additional reference to illustrate that gate oxides can be produced by dry oxidation at 800-1100°C. Wolf, however, does not state that the gate oxides so produced can withstand damage due to total dose radiation as well as SEE, which is a key element of a device according to the present invention. Furthermore, Wolf does not specify that a P-channel device can be modified to include a gate oxide that is less than 1000Å and can resist damage due to total dose radiation as well as SEE. Indeed, Wolf does not at all teach forming radiation hardened gate oxides. It is specifically submitted that in the absence of such teaching or suggestion, one skilled in the art could not modify the teachings of Williams and Kalnitsky as suggested by the Examiner. Reconsideration is, therefore, requested.

Each of the remaining claims depends from claim 1, and, therefore, includes at least its limitations. Furthermore, each dependent claim includes other limitations, which in combination

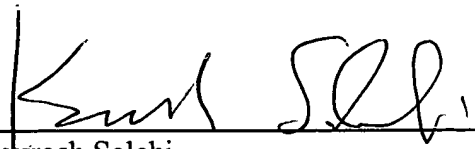
with those of claim 1 are not shown or suggested by the art of record. Reconsideration is requested.

The application is believed to be in condition for allowance. Such action is earnestly solicited.

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Kourosh Salehi
Name of applicant, assignee or Registered Representative

Signature
July 29, 2004
Date of Signature

Respectfully submitted,


Kourosh Salehi
Registration No.: 43,898
OSTROLENK, FABER, GERB & SOFFEN, LLP
1180 Avenue of the Americas
New York, New York 10036-8403
Telephone: (212) 382-0700

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